

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	597	(wafer with anneal\$4 with degrees)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 09:21
L2	118	(wafer with anneal\$4 with degrees with ("300" "500"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 08:30
L3	4	(wafer with anneal\$4 with degrees with ("300" "500") same (pin\$4 magnetic\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 08:33
L4	45	(wafer with anneal\$4 with degrees with ("300" "500") with second)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 08:34
L5	0	(wafer with anneal\$4 with degrees with ("300" "500") with second) and (magnet\$5 with pin\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 08:34
L6	0	(wafer with anneal\$4 with degrees with ("300" "500") with second) same magnet\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 08:36
L7	0	wafer and anneal\$4 and degrees and ("300" "500") and (second sec "s") and magnet\$5	JPO	OR	ON	2007/02/28 08:37
L8	0	wafer and anneal\$4 and ("300" "500") and (second sec "s") and magnet\$5	JPO	OR	ON	2007/02/28 08:37
L9	5	wafer and anneal\$4 and ("300" "500") and (second sec "s")	JPO	OR	ON	2007/02/28 08:39
L10	137	(wafer silicon) and (anneal\$4 treat\$4) and ("300" "500") and (second sec "s")	JPO	OR	ON	2007/02/28 08:41
L11	87	(wafer silicon) and (anneal\$4 treat\$4) and ("300" "500") and (second sec "s") not steel	JPO	OR	ON	2007/02/28 08:42
L12	26	wafer and (anneal\$4 treat\$4) and ("300" "500") and (second sec "s") not steel	JPO	OR	ON	2007/02/28 09:06

EAST Search History

L13	16	wafer and anneal\$4 and (cool\$4 with (liquiid helium nitrogen argon vacuum))	JPO	OR	ON	2007/02/28 09:16
L14	1	wafer and anneal\$4 and (cool\$4 near5 portion)	JPO	OR	ON	2007/02/28 10:54
L15	10	wafer and anneal\$4 and (cool\$4 with (portion section part))	JPO	OR	ON	2007/02/28 09:20
L16	0	wafer and anneal\$4 and (cool\$4 near2 select\$7)	JPO	OR	ON	2007/02/28 09:21
L17	0	wafer and anneal\$4 and (cool\$4 near2 portion)	JPO	OR	ON	2007/02/28 09:21
L18	0	(wafer with anneal\$4 with selectively near2 cool\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 09:22
L19	0	(wafer with anneal\$4 same selectively near2 cool\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 09:22
L20	25	(wafer with anneal\$4 and selectively near2 cool\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 09:22
L21	10	(wafer with anneal\$4 and wafer with selectively near2 cool\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 09:24
L22	0	(wafer with selectively near2 cool\$4)	JPO	OR	ON	2007/02/28 09:25
L23	2	(wafer and selectively near2 cool\$4)	JPO	OR	ON	2007/02/28 09:25
L24	1	("6294911").PN.	USPAT; USOCR	OR	OFF	2007/02/28 10:54
S1	3477	(silicon wafer layer stack) with magnet\$7 with anneal\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:08
S2	58	S1 and ((magnet\$7 near5 anneal\$5) with wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:10

EAST Search History

S3	4	S2 and (anneal\$5 with (lamp laser flashlight rta))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 07:25
S4	268	(magnetoresist\$5 wafer) with magnet\$7 with anneal\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 07:24
S5	11	S4 and (anneal\$5 with (lamp laser flashlight rta))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 07:57
S6	1	("6649423").PN.	USPAT; USOCR	OR	OFF	2005/08/28 07:57
S7	0	S4 and ("spot to spot" "line to line")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:11
S8	0	S1 and ("spot to spot" "line to line")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:11
S9	0	("spot to spot" "line to line")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:11
S10	0	"spot to spot"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:11
S11	11061	spot near2 spot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:12
S12	303338	line near2 line	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:12

EAST Search History

S13	313209	S11 S12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:12
S14	209	S13 with anneal\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:24
S15	3	S13 with anneal\$5 with wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:13
S16	209	S14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:37
S17	7	(S13 with anneal\$5) and (anneal\$5 with wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:25
S18	1987	wafer with (cooled cooling cool) with (helium argon nitrogen vacuum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:38
S19	16	wafer with (cooled cooling cool) with (helium argon nitrogen vacuum) with (anneal\$ near5 temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 09:28
S20	4441	219/121.6,121.65,121.66,121.84, 121.85.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 09:28
S21	1	S20 and (wafer with anneal\$5 with magnet\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 09:29
S22	1	S20 and (wafer with anneal\$5) and (wafer with magnet\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 09:29

EAST Search History

S23	7	S20 and ((silicon layer stack wafer) with anneal\$5) and ((silicon layer stack wafer) with magnet\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 09:30
S24	186741	"438"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:08
S25	2	S24 and (wafer with magnet\$4 with field with anneal\$4).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:15
S26	12	S24 and (wafer with magnet\$4 with field with anneal\$4) not S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:15
S27	12	S24 and (wafer with magnet\$4 near3 field with anneal\$4) not S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:27
S28	5	S26 and (anneal\$5 near5 (entir\$5 local\$4 part portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:33
S29	4	S26 and (anneal\$5 near5 (entir\$5 local\$4 part portion) and degree)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:02
S30	5	S26 and (anneal\$5 near5 (entir\$5 local\$4 part portion) and (anneal\$5 with (temp temperature "C")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:57
S31	1	("6918965").PN.	USPAT; USOCR	OR	OFF	2006/09/20 12:43
S32	1	("4390392").PN.	USPAT; USOCR	OR	OFF	2006/09/20 12:43
S33	2	S31 S32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:44

EAST Search History

S34	1	S33 and magnetic\$5 with anneal\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:44
S35	3	S26 and magnetic\$5 with stack	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:57
S36	3	S26 and (anneal\$5 near5 (select\$9 local\$4 part portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:07
S37	2	S26 and (anneal\$5 near5 (select\$9 local\$4 part portion)) and ((lamp laser light rta flashlight) with anneal\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:09
S38	1	S26 and (anneal\$5 near5 (select\$9 local\$4 part portion)) and ((pin pinned pinning) with (magnetic\$4 layer\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:10
S39	8	S26 and ((pin pinned pinning) with (magnetic\$4 layer\$4)) not S38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:15
S40	2	S26 and (cool\$4 same (liquid helium nitrogen argon vacuum))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:16
S41	25	(magnetic near5 stack) same (cool\$4 same (liquid helium nitrogen argon vacuum))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:16
S42	20	(magnetic near5 stack) same (cool\$4 with (liquid helium nitrogen argon vacuum))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:17
S43	0	(wafer with anneal\$4) and (magnetic near5 stack) same (cool\$4 with (liquid helium nitrogen argon vacuum))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:18

EAST Search History

S44	309	(wafer with anneal\$4) and (wafer with (cool\$4 with (liquid helium nitrogen argon vacuum)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:18
S45	111	(wafer with anneal\$4) and (anneal\$4 same wafer with (cool\$4 with (liquid helium nitrogen argon vacuum)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:19
S46	3	(wafer with anneal\$4) and ((anneal\$4 with (portion point)) same wafer with (cool\$4 with (liquid helium nitrogen argon vacuum)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:21
S47	3	(wafer with anneal\$4) and ((anneal\$4 with (section part portion point)) same wafer with (cool\$4 with (liquid helium nitrogen argon vacuum))) not S46	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:24
S48	3	((anneal\$4 with (section part portion point)) same wafer with (cool\$4 with (liquid helium nitrogen argon vacuum))) not S46	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:24
S49	49	((anneal\$4 with wafer) with (cool\$4 near5 (liquid helium nitrogen argon vacuum))) not S47 not S48	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:25
S50	6197655	b0\$9 b1\$9 b2\$9 b3\$9 b4\$9 b5\$9 b6\$9 b7\$9 b8\$9 b9\$9 f0\$9 f1\$9 f2\$9 f3\$9 f4\$9 f5\$9 f6\$9 f7\$9 f8\$9 f9\$9 g0\$9 g1\$9 g2\$9 g3\$9 g4\$9 g5\$9 g6\$9 g7\$9 g8\$9 g9\$9 h0\$9 h1\$9 h2\$9 h3\$9 h4\$9 h5\$9 h6\$9 h7\$9 h8\$9 h9\$9	JPO	OR	ON	2007/02/26 13:16
S51	989	S50 and (anneal\$4 and (wafer silicon) and magnet\$7)	JPO	OR	ON	2007/02/26 13:17
S52	10	S50 and (anneal\$4 and (wafer silicon) and magnet\$7 with field and magnet\$7 with (layer portion part area))	JPO	OR	ON	2007/02/26 13:26
S53	0	(anneal\$4 and wafer and magnet\$7 with field and magnet\$7 with (layer portion part area)) not S52	JPO	OR	ON	2007/02/27 12:07

EAST Search History

S54	6197655	b0\$9 b1\$9 b2\$9 b3\$9 b4\$9 b5\$9 b6\$9 b7\$9 b8\$9 b9\$9 f0\$9 f1\$9 f2\$9 f3\$9 f4\$9 f5\$9 f6\$9 f7\$9 f8\$9 f9\$9 g0\$9 g1\$9 g2\$9 g3\$9 g4\$9 g5\$9 g6\$9 g7\$9 g8\$9 g9\$9 h0\$9 h1\$9 h2\$9 h3\$9 h4\$9 h5\$9 h6\$9 h7\$9 h8\$9 h9\$9	JPO	OR	ON	2007/02/27 12:07
S55	10	S54 and (anneal\$4 and (wafer silicon) and magnet\$7 with field and magnet\$7 with (layer portion part area))	JPO	OR	ON	2007/02/27 12:07
S56	30	(anneal\$4 and wafer and (magnet\$7 field) with (layer portion part area)) not S55	JPO	OR	ON	2007/02/27 12:09
S57	10	(anneal\$4 and wafer and magnet\$7 and (magnet\$7 field) with (layer portion part area))	JPO	OR	ON	2007/02/27 12:12
S58	6	S54 and (anneal\$4 and wafer with field with (layer portion part area))	JPO	OR	ON	2007/02/27 12:13
S59	0	S54 and (anneal\$4 and wafer with magnet\$7 with field with (layer portion part area))	JPO	OR	ON	2007/02/27 12:13
S60	0	(anneal\$4 and wafer with magnet\$7 with field with (layer portion part area))	JPO	OR	ON	2007/02/27 12:14
S61	152	(anneal\$4 and wafer with magnet\$7 with field with (layer portion part area))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 12:14
S62	46	(anneal\$4 same wafer with magnet\$7 with field with (layer portion part area))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 12:14
S63	34	((anneal\$4 with magnet\$7 with wafer) same (wafer with magnet\$7 with field with (layer portion part area)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 12:15
S64	9	((anneal\$4 with magnet\$7 with wafer) same ((magnet\$7 field) near5 (layer portion part area) near (wafer silicon)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 12:17

EAST Search History

S65	23	wafer with (magnetic adj field) with (magnetic adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 12:18
S66	8	wafer with ((apply\$9 application) near3 magnet\$4) with(magnetic adj field) with (magnetic adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 12:58
S67	1	wafer with ((apply\$9 application) near3 magnet\$4) with (magnetic adj field) same (magnetic near3 layer) same ((local\$9 part\$5 section\$4) near4 layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:14
S68	320	wafer near5 region near5 anneal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:31
S69	62	wafer near2 region near2 anneal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:16
S70	28	anneal\$4 near2 region adj2 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:16
S71	0	wafer near5 region near5 anneal\$4 with pin\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:31
S72	0	wafer near5 region near5 anneal\$4 and (magnet\$4 with pin\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:32
S73	0	wafer near5 region near5 anneal\$4 and pinning	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:32
S74	37	wafer with anneal\$4 same pinning	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:36

EAST Search History

S75	7	wafer with anneal\$4 same pinning and magnet\$9 with vector	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:45
S76	11	(wafer with anneal\$4 same pinning) and (chang\$4 with direction with field)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:48
S77	15	(wafer with anneal\$4 with pin\$4) and (chang\$4 with direction with (magnet\$7 field))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:51
S78	3	(wafer with anneal\$4 with pin\$4) and (align\$4 near5 pin\$5) and (chang\$4 with direction with (magnet\$7 field))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 08:29